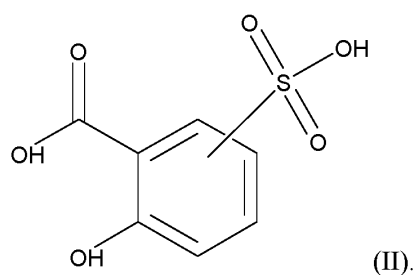
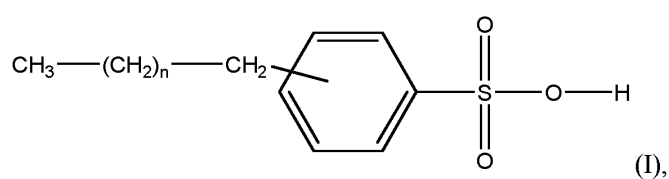
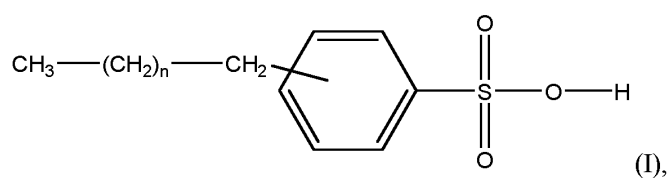


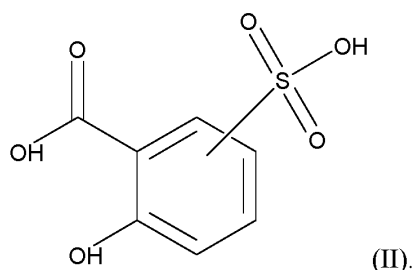
We claim:

1. A composition consisting essentially of
a sulfonic acid selected from the group consisting of
an alkylbenzenesulfonic acid having structure (I), or its hydrate
a sulfosalicylic acid having structure (II), or its hydrate,
and mixtures thereof, wherein n is an integer from 6 to 16, and
the solvent dipropylene glycol dimethyl ether (III),

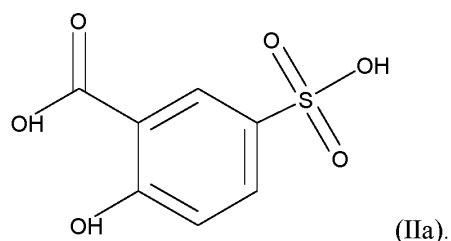


2. A composition consisting essentially of
a sulfonic acid selected from the group consisting of
an alkylbenzenesulfonic acid having structure (I), or its hydrate,
a sulfosalicylic acid having structure (III), or its hydrate,
and mixtures thereof, wherein n is an integer from 6 to 16,
the solvent dipropylene glycol dimethyl ether (III), and
a surfactant;

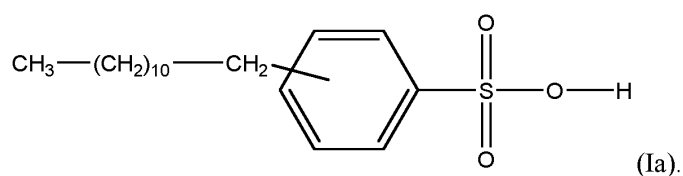




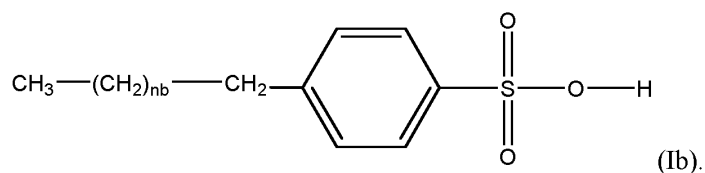
3. The composition of claim 1 consisting of a sulfonic acid selected from the group consisting of an alkylbenzenesulfonic acid having structure (I), or its hydrate, a sulfosalicylic acid having structure (II), or its hydrate, and mixtures thereof, wherein n is an integer from 6 to 16, and the solvent dipropylene glycol dimethyl ether (III).
4. The composition of claim 2 consisting of a sulfonic acid selected from the group consisting of an alkylbenzenesulfonic acid having structure (I), or its hydrate, a sulfosalicylic acid having structure (III), or its hydrate, and mixtures thereof, wherein n is an integer from 6 to 16, the solvent dipropylene glycol dimethyl ether (III), and a surfactant.
5. The composition of any one of claims 1 to 4, wherein said sulfonic acid is an alkylbenzenesulfonic acid having structure (I), or its hydrate.
6. The composition of any one of claims 1 to 4, wherein said sulfonic acid is a sulfosalicylic acid having structure (II), or its hydrate.
7. The composition of any one of claims 1 to 4, wherein said sulfonic acid is a mixture of an alkylbenzenesulfonic acid having structure (I), or its hydrate, and a sulfosalicylic acid having structure (II), or its hydrate.
8. The composition of any one of claims 1, 2, 6 and 7, wherein, for said sulfosalicylic acid, it is one having structure (IIa), or its hydrate,



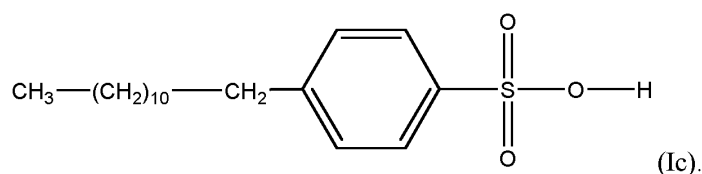
9. The composition of any one of claims 1 to 5, 7, and 8, wherein, for said alkylbenzenesulfonic acid, n is an integer from 8 to 16.
10. The composition of any one of claims 1 to 5, and 7 to 9, wherein, for said alkylbenzenesulfonic acid, n is an integer from 8 to 14.
11. The composition of any one of claims 1 to 5, 7, and 8 to 10, wherein, for said alkylbenzenesulfonic acid, n is an integer from 8 to 10.
12. The composition of any one of claims 1 to 5, and 8 to 11, wherein, for said alkylbenzenesulfonic acid, it has structure (Ia)



13. The composition according to any one of claims 1 to 5, and 8 to 12, wherein for said alkylbenzenesulfonic acid, n is an integer from 6 to 10.
14. The composition according to any one of claims 1 to 5, and 8, wherein said alkylbenzenesulfonic acid has structure (Ib), wherein nb is an integer from 6 to 16;



15. The composition of claim 14 wherein nb is an integer from 10 to 14.
16. The composition of claim 14, wherein nb is an integer from 8 to 10.
17. The composition of any one of claims 14 to 16, wherein said alkylbenzenesulfonic acid has structure (Ic);



18. A process comprising the steps:
- i) heating the composition according to any one of claims 1 to 17, at a temperature which is from about 20°C to about 100°C,
 - ii) treating a substrate coated with a photoresist film with said heated composition for a time from about 1 minutes to about 60 minutes, until a substrate with a removed photoresist film, results,
 - iii) after step ii), rinsing said substrate with a removed photoresist film with either isopropyl alcohol, water or a mixture of isopropyl alcohol and water to remove any residual composition from step ii), producing a clean substrate,
 - iv) drying said clean substrate.
19. The process of claim 18, wherein in step i) the composition is heated from about 30°C to about 65°C.
20. The process of any one of claims 18 to 19, wherein in step ii), the substrate is a metal.
21. The process of any one of claims 18 to 20, wherein in step ii), the substrate is copper.
22. The process of any one of claims 18 to 20, wherein in step ii), the substrate is tin.

23. The process of any one of claims 18 to 22, wherein in step ii), the substrate is treated for about 1 minutes to about 20 minutes.
24. The process of any one of claims 18 to 23, wherein in step iii) the rinse is done with water.
25. The use of the composition of any one of claims 1 to 17 for removing a resist film or a resist pattern from a substrate.